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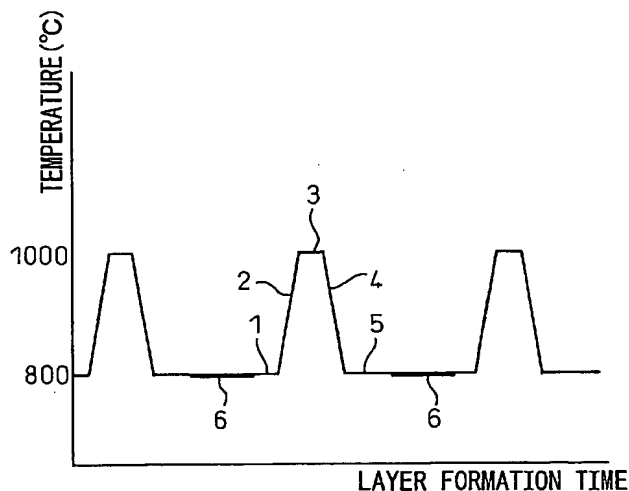
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(54) Title: NITRIDE SEMICONDUCTOR; LIGHT-EMITTING DEVICE, LIGHT-EMITTING DIODE, LASER DEVICE AND LAMP USING THE SEMICONDUCTOR; AND PRODUCTION METHODS THEREOF



(57) Abstract: ABSTRACT An object of the present invention is to provide a nitride semiconductor product which causes no time-dependent deterioration in reverse withstand voltage and maintains a satisfactory initial reverse withstand voltage. The inventive nitride semiconductor product comprises an n-type layer, a light-emitting layer, and a p-type layer which are formed of a nitride semiconductor and sequentially stacked on a substrate in the above order, the light-emitting layer having a quantum well structure in which a well layer is sandwiched by barrier layers having band gaps wider than the band gap of the well layer, wherein each barrier layer comprises a barrier sublayer C which has been grown at a temperature higher than a growth temperature of the well layer, and a barrier sublayer E which has been grown at a temperature lower than a growth temperature of the barrier sublayer C, and the barrier sublayer C is disposed closer to the substrate with respect to the barrier sublayer E.



SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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